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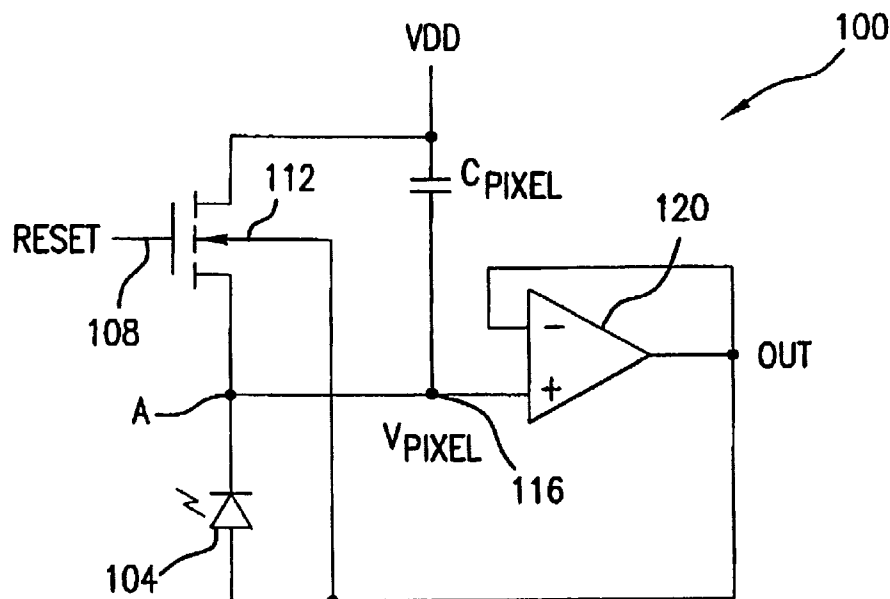
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(54) Title: PIXEL SENSOR WITH A LOW DARK CURRENT PHOTODIODE



(57) Abstract: A method and apparatus for reducing thermally generated dark current in a CMOS imaging device is disclosed. A photodiode within the imaging device is kept zero-biased, so that the voltage is equal at both ends of the photodiode. This zero-biasing is accomplished using several different techniques, including, alternatively: a transistor operating at its sub-threshold level; a leaky diode; a short-channel MOSFET; or ramping charge injection.

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